

SOT-23 Plastic-Encapsulate Transistors**BC846A,B**

TRANSISTOR (NPN)

**BC847A, B, C****BC848A, B, C****FEATURES**

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

**SOT-23****MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)**

Symbol	Para	meter	Value	Units
<b>V<sub>CBO</sub></b>	Collector-Base Voltage	BC846	80	V
		BC847	50	
		BC848	30	
<b>V<sub>CEO</sub></b>	Collector-Emitter Voltage	BC846	65	V
		BC847	45	
		BC848	30	
<b>V<sub>EBO</sub></b>	Emitter-Base Voltage		6	V
<b>I<sub>C</sub></b>	Collector Current –Continuous		0.1	A
<b>P<sub>C*</sub></b>	Collector Power Dissipation		200	mW
<b>T<sub>J</sub></b>	Junction Temperature		150	°C
<b>T<sub>stg</sub></b>	Storage Temperature		-65-150	°C

**DEVICE MARKING**

**BC846A=1A; BC846B=1B;**  
**BC847A=1E; BC847B=1F; BC847C=1G;**  
**BC848A=1J; BC848B=1K; BC848C=1L**

**ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)**

Parameter		Symbol	Test conditions	MIN	TYP	MAX	UNIT
<b>Collector-base breakdown voltage</b>	<b>BC846</b>	V <sub>CBO</sub>	I <sub>C</sub> = 10µA, I <sub>E</sub> =0	80			V
	<b>BC847</b>			50			
	<b>BC848</b>			30			
<b>Collector-emitter breakdown voltage</b>	<b>BC846</b>	V <sub>CEO</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> =0	65			V
	<b>BC847</b>			45			
	<b>BC848</b>			30			
<b>Emitter-base breakdown voltage</b>		V <sub>EBO</sub>	I <sub>E</sub> = 10µA, I <sub>C</sub> =0	6			V
<b>Collector cut-off current</b>	<b>BC846</b>	I <sub>CBO</sub>	V <sub>CB</sub> =70 V , I <sub>E</sub> =0			0.1	µA
	<b>BC847</b>		V <sub>CB</sub> =50 V , I <sub>E</sub> =0				
	<b>BC848</b>		V <sub>CB</sub> =30 V , I <sub>E</sub> =0				
<b>Collector cut-off current</b>	<b>BC846</b>	I <sub>CEO</sub>	V <sub>CE</sub> =60 V , I <sub>B</sub> =0			0.1	µA
	<b>BC847</b>		V <sub>CE</sub> =45 V , I <sub>B</sub> =0				
	<b>BC848</b>		V <sub>CE</sub> =30 V , I <sub>B</sub> =0				
<b>Emitter cut-off current</b>		I <sub>EBO</sub>	V <sub>EB</sub> =5 V , I <sub>C</sub> =0			0.1	µA
<b>DC current gain</b>	<b>BC846A,847A,848A</b>	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 2mA	110		220	
	<b>BC846B,847B,848B</b>			200		450	
	<b>BC847C,BC848C</b>			420		800	
<b>Collector-emitter saturation voltage</b>		V <sub>CE(sat)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> = 5mA			0.5	V
<b>Base-emitter saturation voltage</b>		V <sub>BE(sat)</sub>	I <sub>C</sub> =100mA, I <sub>B</sub> = 5mA			1.1	V
<b>Transition frequency</b>		f <sub>T</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 10mA f=100MHz	100			MHz
<b>Collector output capacitance</b>		C <sub>ob</sub>	V <sub>CB</sub> =10V,f=1MHz			4.5	pF

# Typical Characteristics BC846A,B;BC847A, B, C;BC848A, B, C

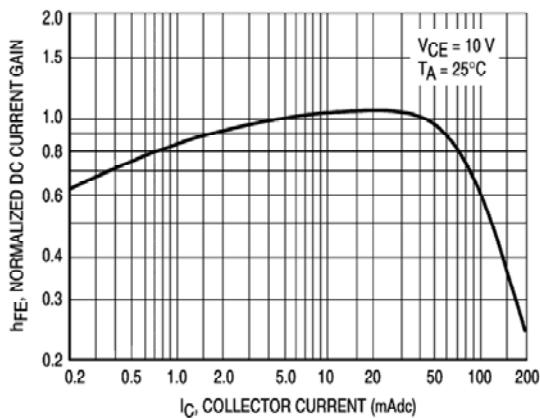


Figure 1. Normalized DC Current Gain

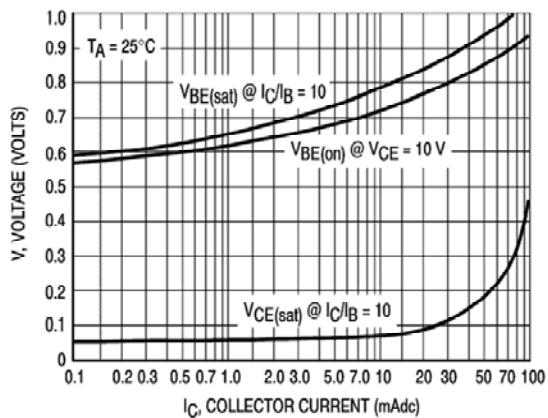


Figure 2. "Saturation" and "On" Voltages

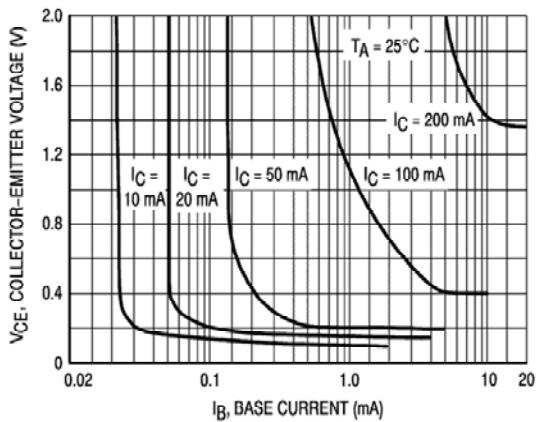


Figure 3. Collector Saturation Region

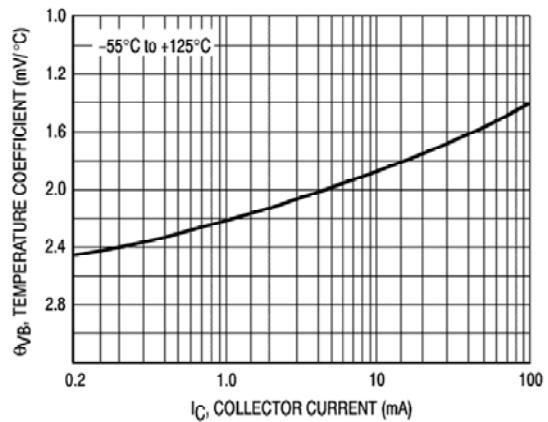


Figure 4. Base-Emitter Temperature Coefficient

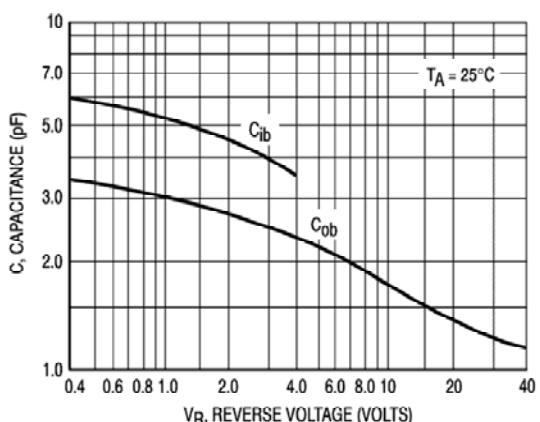


Figure 5. Capacitances

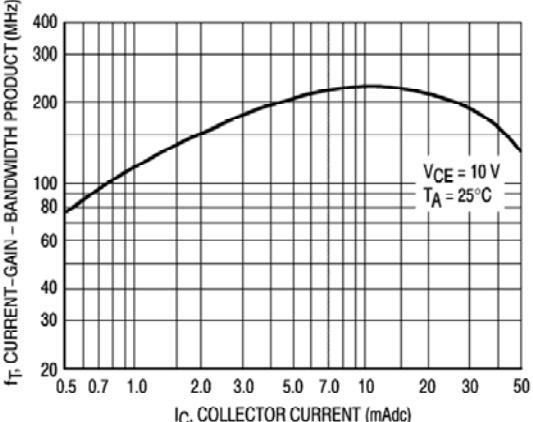


Figure 6. Current-Gain – Bandwidth Product

